

P27127.A05

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Huilong ZHU et al.

Confirmation No.: 1839

Serial No: 10/707,840

Group Art Unit: 2811

Filed: January 16, 2004

Examiner: Nguyen, Dao H.

For: **PROTECTING SILICON GERMANIUM SIDEWALL WITH SILICON FOR
STRAINED SILICON/SILICON GERMANIUM MOSFETS**

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop AF
Randolph Building
401 Dulany Street
Alexandria VA 22314

Sir:

In accordance with the duty of disclosure under 37 C.F.R. § 1.56, and supplemental to the Information Disclosure Statement filed on August 23, 2005, applicant respectfully brings the following documents, listed on the attached form PTO-1449, to the attention of the Examiner in charge of the above-identified application. The Supplemental Information Disclosure Statement is being filed concurrently with a Request for Continued Examination (RCE).

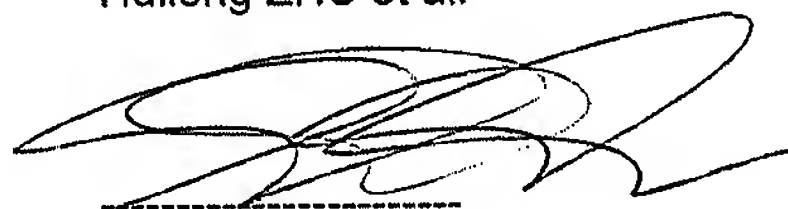
Further to the U.S. Patent and Trademark Office's decision to waive the requirement under 37 C.F.R. § 1.98 (a)(2)(i), copies of the U.S. patents and U.S. published patent applications are not enclosed herewith. However, if any copies are needed, the Examiner is respectfully requested to contact the undersigned.

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Applicants respectfully request that the Examiner consider the materials cited and indicate such consideration by appropriately initialing the enclosed PTO-1449 Form and including a copy of the initialed form in the next official communication.

Should there be any questions concerning this application, the Examiner is invited to contact the undersigned at the below listed telephone number.

Respectfully submitted,
Huilong ZHU et al.

A handwritten signature in black ink, appearing to read 'Andrew M. Calderon', written over a horizontal dashed line.

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FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. P27127	Application No. 10/707,840
	Applicant Huiling ZHU et al.		
	Filing Date January 16, 2004	Group 2811	

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DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

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EXAMINER	DATE CONSIDERED
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*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.		Application No.	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant			
				Filing Date		Group	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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EXAMINER				DATE CONSIDERED			
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